



INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

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Applicant(s)

Daniel C. Edelstein, et al.

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Not Yet Assigned

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER
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Jagannathan, et al., "Self-aligned SiGe NPN Transistors with 285 GHz fMAX and 207 GHz fT in a Manufacturable Technology". IEEE Electron Device letters 23, 259 (2002)

J.S. Rieh, et al., "SiGe HBTs with Cut-off Frequency of 350 GHz", International Electron Device Meeting Technical Digest, 771 (2002)

M.W. Xu et al. "Ultra Low Power SiGe:C HBT for 0.18 um RF-FiCMOS, " Proceedings of the IEEE International Electron Devices Meeting, 2003.

EXAMINER

[Signature]

DATE CONSIDERED

1/15/05

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